



100V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = +25°C		
-100V	350 m Ω @ V _{GS} = -10V	-3.9A		
-1007	450mΩ @ V _{GS} = -6.0V	-3.4A		

Description and Applications

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features and Benefits

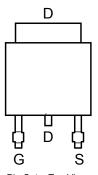
- · Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

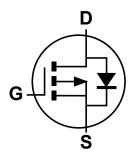
- Case: TO252
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.33 grams (approximate)







Pin Out – Top View



Equivalent Circuit

Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel	
ZXMP10A17KTC	See below	13	16	2,500	

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXMP = Product Type Marking Code, Line 1 10A17 = Product Type Marking Code, Line 2 YYWW = Date Code Marking YY = Year (ex: 09 = 2009) WW = Week (01-52)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

	Characteristic		Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-100	V
Gate-Source Voltage			V _{GS}	±20	V
		(Note 6)		-3.9	
Continuous Drain current	$V_{GS} = 10V$	T _A = +70°C (Note 6)	I_{D}	-3.1	Α
		(Note 5)		-2.4	
Pulsed Drain current V _{GS} = 10V		(Note 7)	I _{DM}	-11.3	Α
Continuous Source Current (Body diode) (Note 6)		Is	-8.7	Α	
Pulsed Source Current (Body diode) (Note 7)		I _{SM}	-11.3	Α	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		4.0 32.0		
Power dissipation Linear derating factor	(Note 6)	P _D	10.2 80.8	W mW/°C	
	(Note 9)		2.0 16.1		
	(Note 5)		31		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	12.3	°C/W	
	(Note 9)		62		
Thermal Resistance, Junction to Case	(Note 8)	$R_{ heta JL}$	2.4	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C	

Notes:

- 5. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is

- measured when operating in a steady-state condition.

 6. Same as note (1), except the device is measured at t ≤ 10 sec.

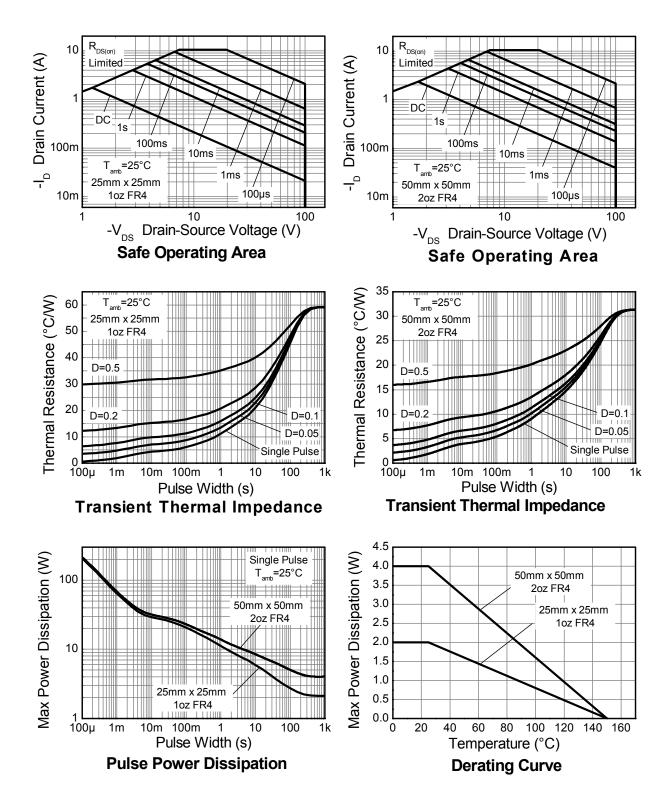
 7. Same as note (1), except the device is pulsed with D= 0.02 and pulse width 300µs. The pulse current is limited by the maximum junction temperature.

 8. Thermal resistance from junction to solder-point (at the end of the drain lead).

 9. For a device surface mounted on 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition. measured when operating in a steady-state condition.



Thermal Characteristics





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

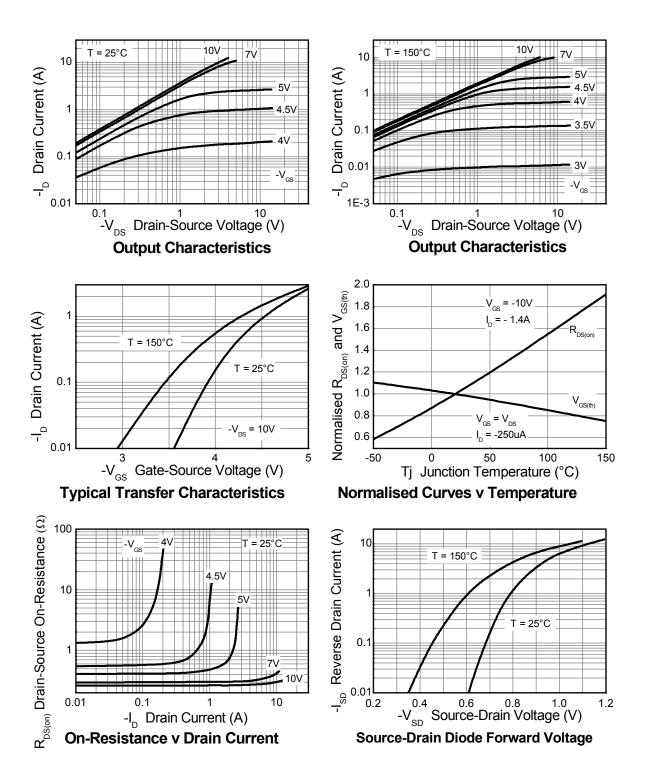
Characteristic	Symbol	Min	Тур	Max	Unit	Test Co	ondition	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage	BV _{DSS}	-100	_	_	V	$I_D = -250 \mu A$, $V_{GS} = 0 V$		
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-0.5	μΑ	V _{DS} = -100V, V _{GS}	s = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	V_{GS} = ±20V, V_{DS}	= 0V	
ON CHARACTERISTICS								
Gate Threshold Voltage	V _{GS(th)}	-2.0	_	-4.0	٧	$I_D = -250 \mu A, V_{DS}$	= V _{GS}	
Static Drain-Source On-Resistance (Note 10)	В			0.350	Ω	$V_{GS} = -10V, I_D = -10V$	-1.4A	
Static Dialit-Source Off-Resistance (Note 10)	R _{DS(ON)}	_	_	0.450	22	$V_{GS} = -6V, I_D = -1$.2A	
Forward Transconductance (Notes 10 & 11)	g _{fs}	_	2.8	_	S	$V_{DS} = -15V, I_{D} = -15V$	-1.4A	
Diode Forward Voltage (Note 10)	V_{SD}	_	-0.85	-0.95	٧	I _S = -1.7A, V _{GS} = 0V		
Reverse recovery time (Note 11)	t _{rr}		33	_	ns	I _S = -1.5A, di/dt = 100A/µs		
Reverse recovery charge (Note 11)	Qrr	_	48	_	nC			
DYNAMIC CHARACTERISTICS (Note 11)								
Input Capacitance	C _{iss}	_	424	_	pF	50/1/ 01/		
Output Capacitance	Coss	_	36.6	_	pF	V _{DS} = -50V, V _{GS} = 0V - F = 1MHz		
Reverse Transfer Capacitance	C _{rss}	_	29.8	_	pF	1 - 11VII 12		
Total Gate Charge (Note 12)	Q_g	_	7.1	_	nC	$V_{GS} = -6.0V$		
Total Gate Charge (Note 12)	Qg	_	10.7	_	nC		V _{DS} = -50V	
Gate-Source Charge (Note 12)	Qgs	_	1.7	_	nC	V _{GS} = -10V I _D = -1.4A		
Gate-Drain Charge (Note 12)	Q_{gd}	_	3.8	_	nC]		
Turn-On Delay Time (Note 12)	t _{D(on)}	_	3.0	_	ns			
Turn-On Rise Time (Note 12)	t _r	_	3.5	—	ns	V _{DD} = -50V, V _{GS} = -10V		
Turn-Off Delay Time (Note 12)	t _{D(off)}	_	13.4	_	ns	$I_D = -1A, R_G \cong 6.0\Omega$		
Turn-Off Fall Time (Note 12)	t _f	_	7.2		ns	1		

Notes:

- 10. Measured under pulsed conditions. Pulse width \leq 300µs; duty cycle \leq 2% 11. For design aid only, not subject to production testing. 12. Switching characteristics are independent of operating junction temperatures.

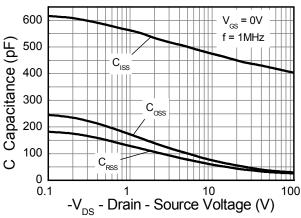


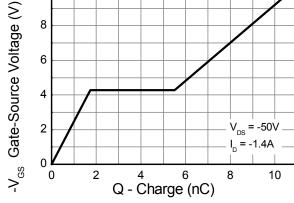
Typical Characteristics





Typical Characteristics (cont.)



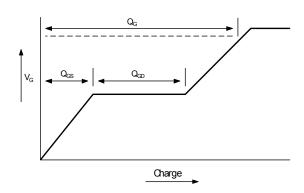


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Capacitance v Drain-Source Voltage

Gate-Source Voltage v Gate Charge

Test Circuits

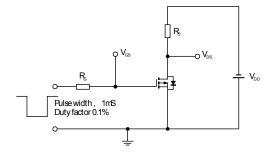


Current regulator 50k ₹ D.U.T

Basic gate charge waveform

 V_{DS} 10%

Gate charge test circuit

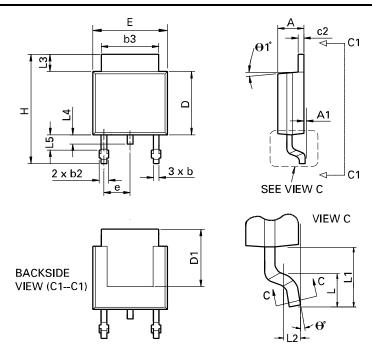


Switching time waveforms

Switching time test circuit

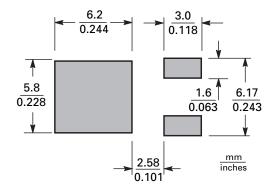


Package Outline Dimensions



DIM	Inches		Millimeters		DIM	Inches		Millimeters		
DIN	Min	Max	Min	Max	DIIVI	Min	Max	Min	Max	
Α	0.086	0.094	2.18	2.39	е	0.090 BSC		2.29 BSC		
A1	-	0.005	-	0.127	Н	0.370	0.410	9.40	10.41	
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78	
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF		
b3	0.205	0.215	5.21	5.46	L2	0.020	0.020 BSC		0.508 BSC	
С	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65	
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016	
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52	
D1	0.205	-	5.21	-	θ1°	0°	10°	0°	10°	
E	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°	
E1	0.170	-	4.32	-	-	-	-	-	-	

Suggested Pad Layout





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